

CN850-40P

INFRARED LED CHIP

<Specifications>

Commodity Type and Physical Characteristics	
Material	GaAlAs/GaAlAs(DDH)
Top Side P(anode)side	Au Alloy
Bottom Side N(cathode)side	Au Alloy
Electrode Pattern	Fig.1
Chip Size	Fig.2
Chip Thickness	Fig.2
Emission Area	Fig.2

Electro-Optical Characteristics[Ta=25°C]						
Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	Vf	IF=20mA		1.35	1.6	V
Reverse Current	IR	VR=5V			10	uA
Power Intensity	PO	IF=20mA	3.0	6.0		mW
Peak Wavelength	λP	IF=20mA	840	850	860	nm
Spectral Radiation Bandwidth	$\Delta\lambda$	IF=20mA		40		nm
Rise Time	tr	IF=20mA		15		ns
Fall Time	tf	IF=20mA		10		ns

Die shall be mounted on TO-18 gold header without resin coated.

[Unit: um]

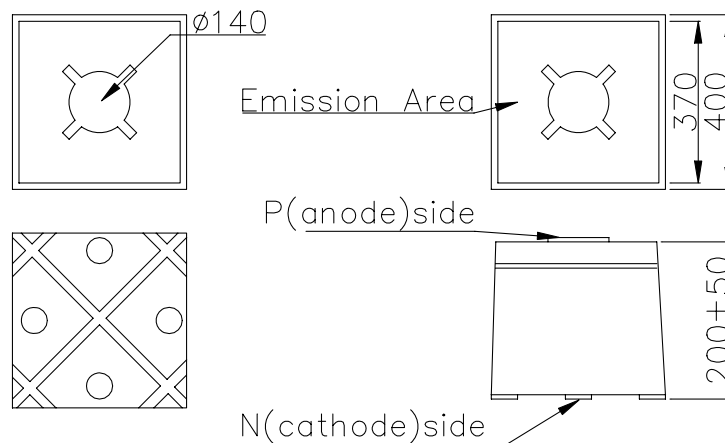


Fig.1 Electrode Pattern

Fig.2 Chip size and Emission Area